Ref. No.: Ex/Prod/ET/T/125/2019(Old) B.E. PRODUCTION ENGINEERING FIRST YEAR SECOND SEMESTER (Old) EXAM 2019

Subject: Basic Electronics Engineering

All parts of the same question must be answered at one place only	wiarks: 100
I. Answer any two(2) from Q. 1 (a), (b) and (c) in this block:	
 1. (a) i Cut-in voltage of silicon and germanium PN junction diode is and ii. In P type semiconductors, the majority carriers are and, in N type semiconductors, the majority carriers are iv. Differentiate semiconductor, conductor and insulator. v. Define hole and electron in a semiconductor. 	
	[4+3+3]
 (b) i. An ideal diode offers resistance when forward biased, and resistance when reverse biased. ii. Draw and explain the VI characteristics of a PN junction diode. iii. What is an intrinsic semiconductor? iv. What are the majority carrier and minority carrier of p type and n type 	nen it is
semiconductor.	[2+4+2+2]
 (c) i. What is doping? Why it is needed? ii. Name the elements which are used as N-type impurities and P-type impurities. iii. Explain the operation of a PN junction diode under no bias condition. iv. What is meant by the term "Barrier potential"? What is it value for Germanium diode? II. Answer any three(3) from 2 (a), (b), (c) and (d) in this block: 2. (a) i. Draw the circuit diagram of centre tap half-wave rectifier and explain its operation. ii. Discuss the working of full-wave rectifier circuit and give the output voltage waveform. iii. Define breakdown voltage. 	
 (b) i. State whether the statement is true or false: i.i A transistor has two PN junction. i.ii The emitter of a transistor is heavily doped. i.iii Base has the biggest size in a transistor. i.iv The value of α of a transistor is less than 1. ii. Draw and explain a fixed bias circuit. 	[4+6]
 (c) i. Explain the CE configuration of BJT with circuit diagram, input and output character ii. Derive the relation between α, β. [6+4] 	istics.
 (d) i. State whether the statement is true or false: i.i In P-type semiconductor, the majority carriers are hole. i.ii A full-wave rectifier utilizes only positive half cycle. i.iii For a half-wave rectifier: PIV = 2V_m. 	

[4+4+2]

[3+3+4]

[2+2+3+3]

Distinguish between zener breakdown and avalanche breakdown.

iii. What is Q point?

ii. What is a flip-flop?

III. Answer 3 (a) OR (b) in this block:

3. (a) i. Compare class A, class B and class C amplifier. ii. Define cross over distortion and how it can be overcome? iii. What do you mean by efficiency in power amplifier? [4+3+3] (b) i. Explain the working of schmit trigger with proper circuit diagram ii. Describe the working of a stable multivibrator with a neat circuit diagram [3+3+4]IV. Answer any three (03) from 4 (a), (b), (c) and (d) in this block: 4. (a) i. Convert base of the following numbers: i.i. $(64.5)_{10} \equiv (?)_2$ i.ii. $(7CA3)_{16} \equiv (?)_8$ i.iii. $(742.46)_8 \equiv (?)_2$ ii. Obtain 2's complement of (1010100)₂ and (1101001)₂. iii. Subtract (i) (1110)₂ from (10101)₂ and (ii) (10011)₂ from (11101)₂ (without converting base). (b) i. State De-Morgan's theorem. Show its logic implementation. ii. Simplify the following Boolean expression: $f = (A + \overline{B}C) + (\overline{A + \overline{B}C})$ and $f = AB + ABC + \overline{A}B + A\overline{B}C$ [4+6] (c) i. Realize the following two Boolean expressions using basic gates f = (C(A+B)+D) and $f = (\overline{AB} + + \overline{C})$ ii. Add (a) (38)10 and (17)10 and (b) (84)10 and (53)10 using BCD numbers. [6+4] (d) i. Draw the symbols of universal gates. Write their truth table (for 2-input gate). ii. Realize AND, OR and NOT using only NAND gates. [4+6] V. Answer 5.(a) OR (b) from this block: 5. (a) i. Distinguish between combinational circuit and sequential circuits.

iii. Describe the working of SR flip-flop with circuit diagram and truth table.

(b) i. What is the difference between latch and flip-flop?ii. What is a clock? What is the purpose of the clock signal?

iii. Draw the circuit diagram of JK flip-flop. iv. What is race around in JK flip-flop?